HEF4541B-Q100

Programmable timer

Rev. 2 — 31 December 2013 Product data sheet

1. General description

The HEF4541B-Q100 is a programmable timer. It consists of a 16-stage binary counter, an integrated oscillator to be used with external timing components, an automatic power-on reset and output control logic. The external components R_{TC} and C_{TC} determines the frequency of the oscillator within the frequency range 1 Hz to 100 kHz. An external clock signal at input RS can replace the oscillator. The timer advances on the positive-going transition of RS. A LOW on the auto reset input (AR) and a LOW on the master reset input (MR) enables the internal power-on reset. A HIGH level at input MR resets the counter independent on all other inputs. Resetting, disables the oscillator to provide no active power dissipation.

A HIGH at input AR turns off the power-on reset to provide a low quiescent power dissipation of the timer. The 16-stage counter divides the oscillator frequency by 2^8, 2^{10}, 2^{13} or 2^{16} depending on the state of the address inputs (A0, A1). The divided oscillator frequency is available at output O. The phase input (PH) features a complementary output signal. When the mode select input (MODE) is LOW the timer is a single transition timer and when HIGH the timer is a 2^n frequency divider.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD}, V_{SS}, or another input.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Complies with JEDEC standard JESD 13-B

3. Ordering information

Table 1. Ordering information

All types operate from −40 °C to +125 °C.

Type number	Package		
	Name	Description	Version
HEF4541BT-Q100	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1

4. Functional diagram

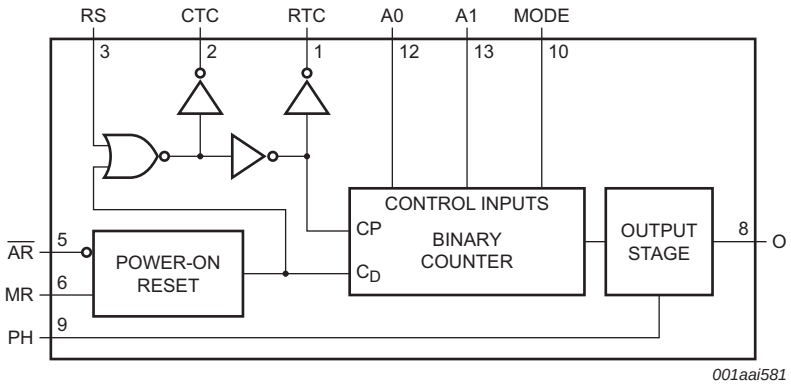


Fig 1. Functional diagram

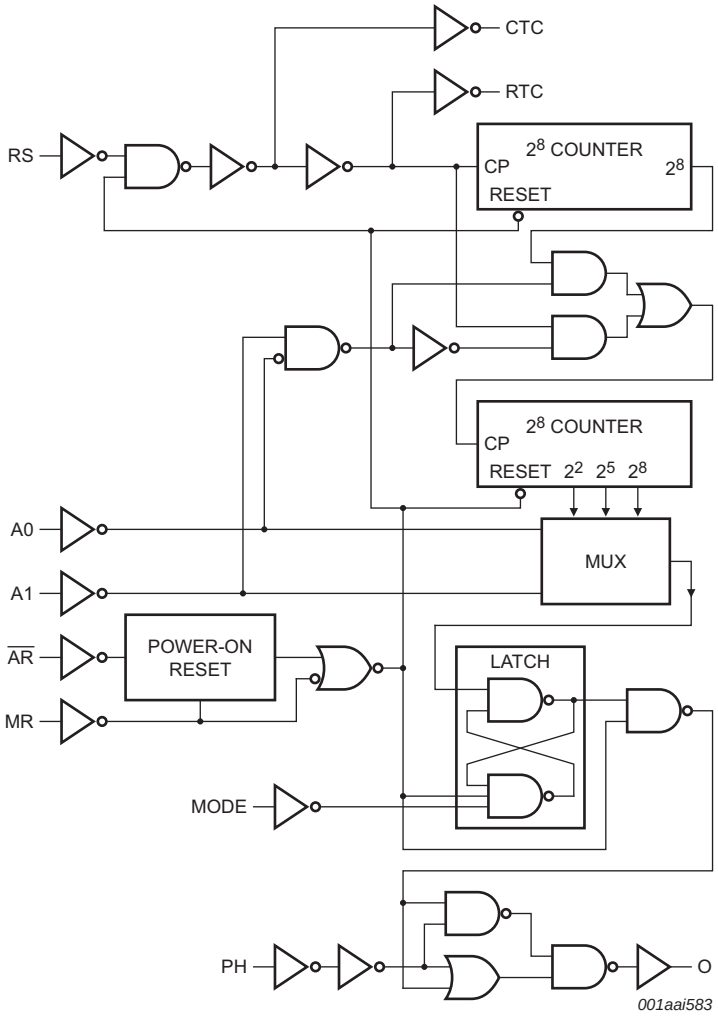


Fig 2. Logic diagram

5. Pinning information

5.1 Pinning

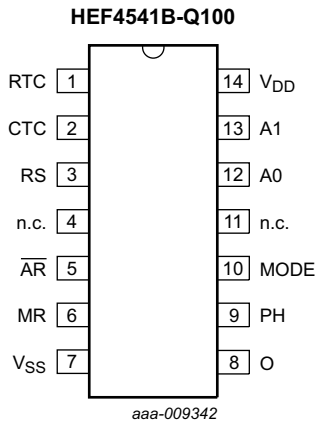


Fig 3. Pin configuration

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
RTC	1	external resistor connection
CTC	2	external capacitor connection
RS	3	external resistor connection (RS) or external clock input
nc	4, 11	not connected
$\overline{AR}$	5	auto reset input (active low)
MR	6	master reset input
V_{SS}	7	ground (0 V)
O	8	timer output
PH	9	phase input
MODE	10	mode select input
A0, A1	12, 13	address inputs
V_{DD}	14	supply voltage

6. Functional description

Table 3. Function table[1]

Input				MODE
$\overline{AR}$	MR	PH	MODE	
H	L	X	X	auto reset disabled
L	L	X	X	auto reset enabled[2]
X	H	X	X	master reset active
X	L	X	H	normal operation selected division to output
X	L	X	L	single-cycle mode[3]
X	L	L	X	output initially LOW after reset
X	L	H	X	output initially HIGH, after reset

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

[2] For correct power-on reset, the supply voltage should be above 8.5 V. For V_{DD} < 8.5 V, disable the auto reset and connect $\overline{AR}$ to V_{DD}.

[3] The timer is initialized on a reset pulse and the output changes state after 2^{n-1} counts and remains in that state (latched). A master reset or a LOW to HIGH transition on the MODE input, resets this latch.

Table 4. Frequency selection table

A0	A1	Number of counter stages n	$\frac{f_{OSC}}{f_O} = 2^n$
L	L	13	8192
L	H	10	1024
H	L	8	256
H	H	16	65536

7. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DD}	supply voltage			–0.5	+18	V
I_{IK}	input clamping current	V_I < –0.5 V or V_I > V_{DD} + 0.5 V		-	±10	mA
V_I	input voltage			–0.5	V_{DD} + 0.5	V
I_{OK}	output clamping current	V_O < –0.5 V or V_O > V_{DD} + 0.5 V		-	±10	mA
$I_{I/O}$	input/output current	O output		-	±10	mA
T_{stg}	storage temperature			–65	+150	°C
T_{amb}	ambient temperature			–40	+125	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C	[1]	-	500	mW
P	power dissipation			-	100	mW

[1] For SO14 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

8. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		3	15	V
V_I	input voltage		0	V_{DD}	V
T_{amb}	ambient temperature	in free air	–40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{DD} = 5 V	-	3.75	µs/V
		V_{DD} = 10 V	-	0.5	µs/V
		V_{DD} = 15 V	-	0.08	µs/V

9. Static characteristics

Table 7. Static characteristics

V_{SS} = 0 V; V_I = V_{SS} or V_{DD}; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	T_{amb} = –40 °C		T_{amb} = 25 °C		T_{amb} = 85 °C		T_{amb} = 125 °C		Unit
				Min	Max	Min	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage	$\|I_O\|$ < 1 µA	5 V	3.5	-	3.5	-	3.5	-	3.5	-	V
			10 V	7.0	-	7.0	-	7.0	-	7.0	-	V
			15 V	11.0	-	11.0	-	11.0	-	11.0	-	V
V_{IL}	LOW-level input voltage	$\|I_O\|$ < 1 µA	5 V	-	1.5	-	1.5	-	1.5	-	1.5	V
			10 V	-	3.0	-	3.0	-	3.0	-	3.0	V
			15 V	-	4.0	-	4.0	-	4.0	-	4.0	V
V_{OH}	HIGH-level output voltage	$\|I_O\|$ < 1 µA	5 V	4.95	-	4.95	-	4.95	-	4.95	-	V
			10 V	9.95	-	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	14.95	-	V
V_{OL}	LOW-level output voltage	$\|I_O\|$ < 1 µA	5 V	-	0.05	-	0.05	-	0.05	-	0.05	V
			10 V	-	0.05	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	-	0.05	V
I_{OH}	HIGH-level output current	CTC, RTC;										
		V_O = 2.5 V	5 V	-	–1.4	-	–1.2	-	–0.95	-	–0.95	mA
		V_O = 4.6 V	5 V	-	–0.5	-	–0.4	-	–0.3	-	–0.3	mA
		V_O = 9.5 V	10 V	-	–1.4	-	–1.2	-	–0.95	-	–0.95	mA
		V_O = 13.5 V	15 V	-	–4.8	-	–4.0	-	–3.2	-	–3.2	mA
		O;										
		V_O = 2.5 V	5 V	-	–1.7	-	–1.4	-	–1.1	-	–1.1	mA
		V_O = 4.6 V	5 V	-	–0.64	-	–0.5	-	–0.36	-	–0.36	mA
		V_O = 9.5 V	10 V	-	–1.6	-	–1.3	-	–0.9	-	–0.9	mA
		V_O = 13.5 V	15 V	-	–4.2	-	–3.4	-	–2.4	-	–2.4	mA

Table 7. Static characteristics *...continued*

V_{SS} = 0 V; V_I = V_{SS} or V_{DD}; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	T_{amb} = –40 °C		T_{amb} = 25 °C		T_{amb} = 85 °C		T_{amb} = 125 °C		Unit
				Min	Max	Min	Max	Min	Max	Min	Max	
I_{OL}	LOW-level output current	CTC, RTC;										
		V_O = 0.4 V	5 V	0.33	-	0.27	-	0.20	-	0.20	-	mA
		V_O = 0.5 V	10 V	1.0	-	0.85	-	0.68	-	0.68	-	mA
		V_O = 1.5 V	15 V	3.2	-	2.7	-	2.3	-	2.3	-	mA
		O;										
		V_O = 0.4 V	5 V	0.64	-	0.5	-	0.36	-	0.36	-	mA
		V_O = 0.5 V	10 V	1.6	-	1.3	-	0.9	-	0.9	-	mA
		V_O = 1.5 V	15 V	4.2	-	3.2	-	2.4	-	2.4	-	mA
I_I	input leakage current		15 V	-	±0.1	-	±0.1	-	±1.0	-	±1.0	µA
I_{DD}	supply current	I_O = 0 A	5 V	-	5	-	5	-	150	-	150	µA
			10 V	-	10	-	10	-	300	-	300	µA
			15 V	-	20	-	20	-	600	-	600	µA
C_I	input capacitance		-	-	-	-	7.5	-	-	-	-	pF

Table 8. Reset characteristics

V_{SS} = 0 V; V_I = V_{SS} or V_{DD}; see Table 12 for test conditions; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	T_{amb} = –40 °C		T_{amb} = +25 °C			T_{amb} = +85 °C		T_{amb} = +125 °C		Unit
				Min	Max	Min	Typ	Max	Min	Max	Min	Max	
I_{DD}	supply current	supply current for power-on reset enable; $\overline{AR}$ = MR = 0 V; Other inputs at 0 V or V_{DD}	5 V	-	80	-	20	80	-	230	-	230	µA
			10 V	-	750	-	250	600	-	700	-	700	µA
			15 V	-	1.6	-	0.5	1.3	-	1.5	-	1.5	mA
V_{DD}	supply voltage	supply voltage for automatic reset initialization; $\overline{AR}$ = MR = 0 V; Other inputs at 0 V or V_{DD}	-	-	-	8.5	5	-	-	-	-	-	V

10. Dynamic characteristics

Table 9. Dynamic characteristics

V_{SS} = 0 V; T_{amb} = 25 °C unless otherwise specified. For test circuit, see Figure 5.

Symbol	Parameter	Conditions	V_{DD}		Extrapolation formula	Min	Typ[1]	Max	Unit
t_{pd}	propagation delay	RS to O; 2^8 selected; see Figure 4	5 V	[2]	348 ns + (0.55 ns/pF)C_L	-	375	750	ns
			10 V		139 ns + (0.23 ns/pF)C_L	-	150	300	ns
			15 V		102 ns + (0.16 ns/pF)C_L	-	110	220	ns
		RS to O; 2^{10} selected; see Figure 4	5 V		398 ns + (0.55 ns/pF)C_L	-	425	850	ns
			10 V		154 ns + (0.23 ns/pF)C_L	-	165	330	ns
			15 V		112 ns + (0.16 ns/pF)C_L	-	120	240	ns
		RS to O; 2^{13} selected; see Figure 4	5 V		483 ns + (0.55 ns/pF)C_L	-	510	1020	ns
			10 V		179 ns + (0.23 ns/pF)C_L	-	190	380	ns
			15 V		127 ns + (0.16 ns/pF)C_L	-	135	270	ns
		RS to O; 2^{16} selected; see Figure 4	5 V		548 ns + (0.55 ns/pF)C_L	-	575	1150	ns
			10 V		199 ns + (0.23 ns/pF)C_L	-	210	420	ns
			15 V		142 ns + (0.16 ns/pF)C_L	-	150	300	ns
t_W	pulse width	RS LOW; MR HIGH; see Figure 4	5 V	[3]		60	30	-	ns
			10 V			30	15	-	ns
			15 V			24	12	-	ns
$f_{clk(max)}$	maximum clock frequency	RS; see Figure 4	5 V			8	16	-	MHz
			10 V			15	30	-	MHz
			15 V			18	36	-	MHz
f_{osc}	oscillator frequency	R_t = 5 kΩ; C_t = 1 nF; R_S = 10 kΩ; see Figure 6	5 V			-	90	-	kHz
			10 V			-	90	-	kHz
			15 V			-	90	-	kHz
		R_t = 56 kΩ; C_t = 1 nF; R_S = 120 kΩ; see Figure 6	5 V			-	8	-	kHz
			10 V			-	8	-	kHz
			15 V			-	8	-	kHz

[1] The typical values of the propagation delay and transition times are calculated from the extrapolation formulas shown (C_L in pF).

[2] t_{pd} is the same as t_{PHL} and t_{PLH}.

[3] t_W is the same as $t_{WL(min)}$ and $t_{WH(min)}$.

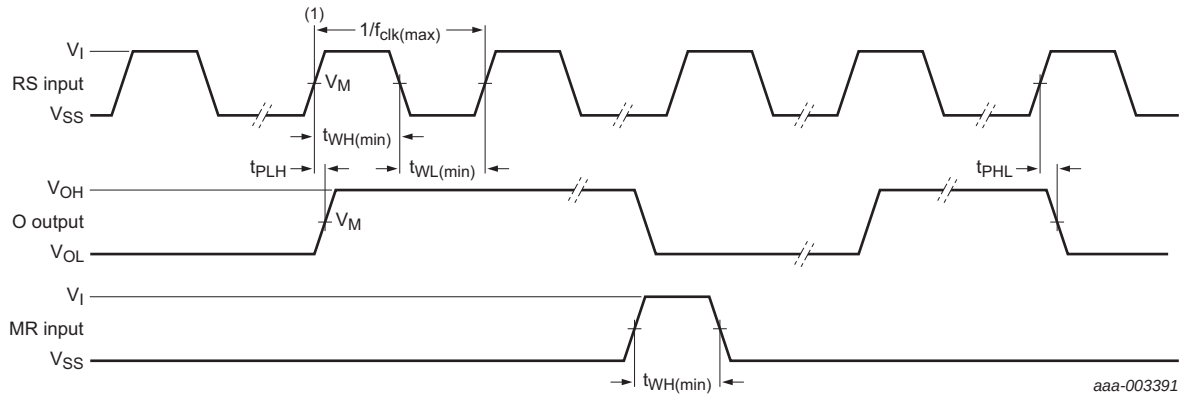
Table 10. Dynamic power dissipation

P_D can be calculated from the formulas shown. V_{SS} = 0 V; $t_r = t_f \leq 20$ ns; T_{amb} = 25 °C.

Symbol	Parameter	V_{DD}	Typical formula
P_D	dynamic power dissipation	Per package	
		5 V	$P_D = 1300 \times f_i + (f_o \times C_L \times V_{DD}^2)$ µW
		10 V	$P_D = 5300 \times f_i + (f_o \times C_L \times V_{DD}^2)$ µW
		15 V	$P_D = 12000 \times f_i + (f_o \times C_L \times V_{DD}^2)$ µW
		Total, using the on-chip oscillator	
		5 V	$P_D = 1300 \times f_{osc} + f_o C_L V_{DD}^2 + 2C_{TC} V_{DD}^2 f_{osc} + 10 V_{DD}$ µW
		10 V	$P_D = 5300 \times f_{osc} + f_o C_L V_{DD}^2 + 2C_{TC} V_{DD}^2 f_{osc} + 100 V_{DD}$ µW
		15 V	$P_D = 12000 \times f_{osc} + f_o C_L V_{DD}^2 + 2C_{TC} V_{DD}^2 f_{osc} + 400 V_{DD}$ µW

[1] f_i = input frequency in MHz; f_o = output frequency in MHz; C_L = output load capacitance in pF; V_{DD} = supply voltage in V; f_{osc} = oscillator frequency in MHz; C_{TC} = timing capacitance in pF.

11. Waveforms



V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

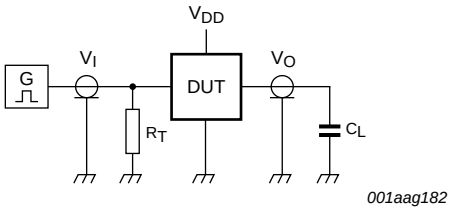
Measurement points are given in Table 11, the test circuit in Figure 5 and the test data in Table 12

(1) 2^n pulses as selected by address inputs (A0, A1).

Fig 4. Propagation delay clock (RS) to output (O), clock pulse width and maximum clock frequency

Table 11. Measurement points

Supply voltage	Input	Output
V_{DD}	V_M	V_M
5 V to 15 V	$0.5V_{DD}$	$0.5V_{DD}$



Test data is given in Table 12.

Definitions for test circuit:

DUT - Device Under Test.

R_L = Load resistance.

C_L = load capacitance.

R_T = Termination resistance should be equal to output impedance of Z_o of the pulse generator.

Fig 5. Test circuit for measuring switching times

Table 12. Test data

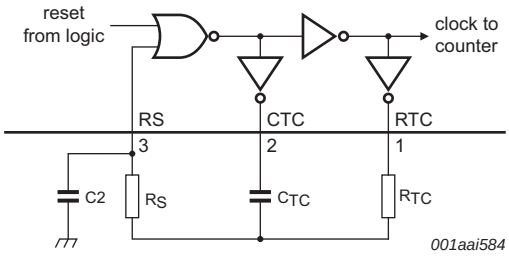
Supply	Input		Load
V_{DD}	V_I	t_r, t_f	C_L
5 V to 15 V	V_{SS} or V_{DD}	≤ 20 ns	50 pF

12. Application information

RC oscillator timing component limitations

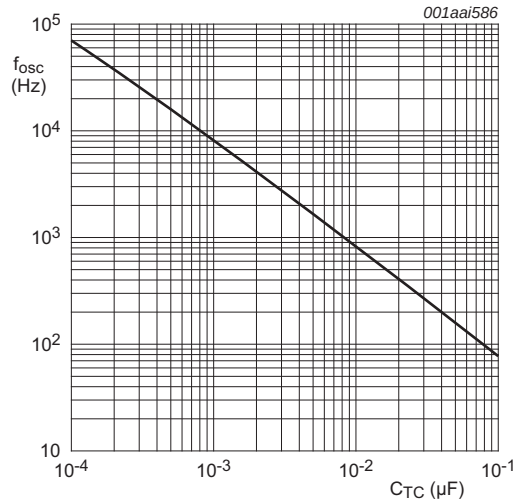
$R_{TC}C_{TC}$ determines the oscillator frequency, provided $R_{TC} << R_S$ and $R_SC_2 << R_{TC}C_{TC}$. The function of R_S is to minimize the influence of the forward voltage across the input protection diodes on the frequency. The stray capacitance C_2 should be kept as small as possible. In consideration of accuracy, C_{TC} must be larger than the inherent stray capacitance. R_{TC} must be larger than the LOCMOS 'ON' resistance in series with it, which typically is 500 Ω at V_{DD} = 5 V, 300 Ω at V_{DD} = 10 V and 200 Ω at V_{DD} = 15 V.

The recommended values for these components to maintain agreement with the typical oscillation formula are: $C_{TC} \geq 100$ pF, up to any typical value, 10 kΩ ≤ R_{TC} ≤ 1 MΩ.

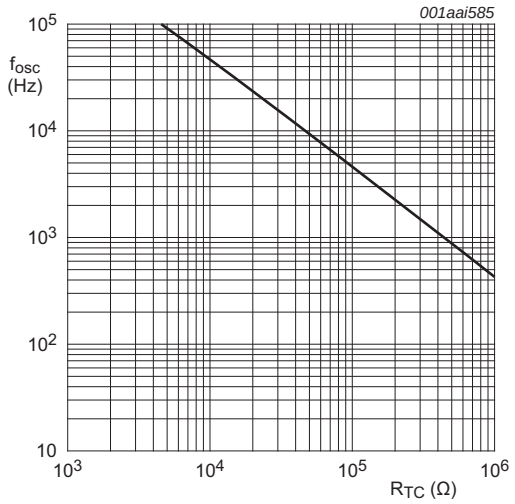


Typical formula for oscillator frequency: $f_{osc} = \frac{1}{2.3 \times R_{TC} \times C_{TC}}$.

Fig 6. External component connection for RC oscillator; $R_S \approx R_{TC}$

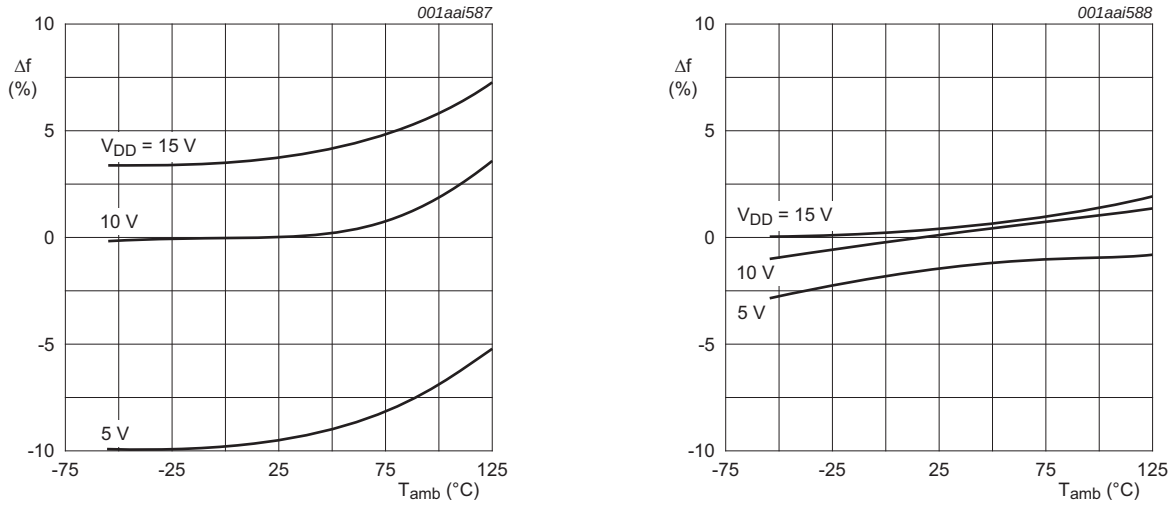


a. C_{TC} curve at R_{TC} = 56 kΩ; RS = 120 kΩ.



b. R_{TC} curve at C_{TC} = 1 nF; RS = 2 R_{TC}.

Fig 7. RC oscillator frequency as a function of R_{TC} and C_{TC} at V_{DD} = 5 V to 15 V; T_{amb} = 25 °C



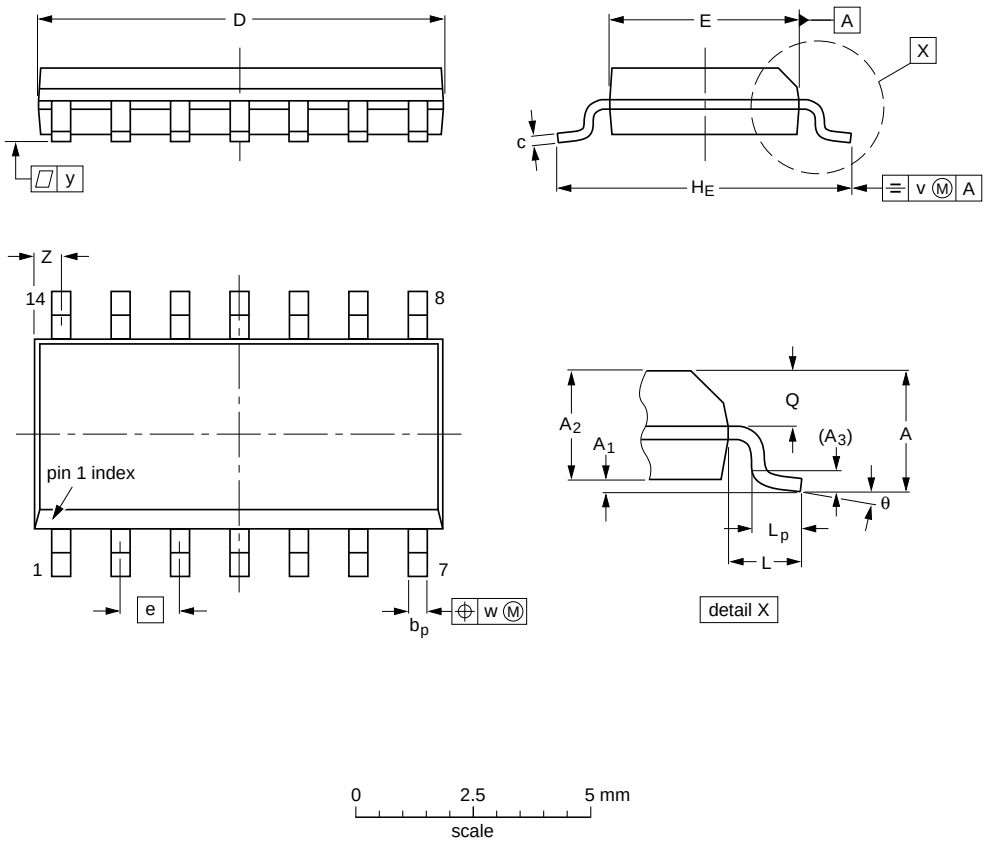
a. R_{TC} = 56 kΩ; C_{TC} = 1 nF; RS = 0 Ω.

b. R_{TC} = 56 kΩ; C_{TC} = 1 nF; RS = 120 kΩ.

Fig 8. Frequency deviation (Δf) as a function of ambient temperature

13. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm **SOT108-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT108-1	076E06	MS-012				~~99-12-27~~ 03-02-19

Fig 9. Package outline SOT108-1 (SO14)

14. Abbreviations

Table 13. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4541B_Q100 v.2	20131231	Product data sheet	-	HEF4541B_Q100 v.1
Modifications:	• Maximum temperature changed to 125 °C throughout.			
HEF4541B_Q100 v.1	20131021	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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